



F. Silicon and Group-IV Devices and Integration Technology 분과

2021년 1월 28일(목), 16:30-18:00 / 채널 B

[TB5-F] Reliability/Variability Characterization

좌장: 권대웅 교수 (인하대학교), 김가람 교수 (명지대학교)

<p>TB5-F-1 16:30-16:45</p>	<p>Visibly Transparent Amorphous Silicon via Passivation of Dangling Bonds Enabling Low-Loss Photonic Platforms at the Visible Frequencies</p> <p>Younghwan Yang¹, Gwanho Yoon¹, Sunghak Park², Ki Tae Nam², and Junsuk Rho¹ ¹<i>Department of Mechanical Engineering, POSTECH,</i> ²<i>Department of Material Science and Engineering, Seoul National University</i></p>
<p>TB5-F-2 16:45-17:00</p>	<p>Modeling of Statistical Variation Effects on DRAM Sense Amplifier Offset Voltage</p> <p>Kyung Min Koo¹, Woo Young Chung², Sang Yi Lee², Gyu Han Yoon¹, and Woo Young Choi¹ ¹<i>Department of Electronic Engineering, Sogang University,</i> ²<i>Department of DRAM Sensing & Advanced Analysis, SK Hynix Inc.</i></p>
<p>TB5-F-3 17:00-17:15</p>	<p>Effects of Deuterium on the Random Telegraph Signal Noise Characteristics of FD-SOI pTFETs</p> <p>Hyun-Jin Shin, Ki-Woo Song, Hyun-Woong Choi, Seong-Hyun Kim, and Hi-Deok Lee <i>Department of Electronics Engineering, Chungnam National University</i></p>
<p>TB5-F-4 17:15-17:30</p>	<p>A New Approach to Estimate the Process-Induced Random Variation in Current-voltage Characteristic of FinFET: Machine-Learning Technique</p> <p>Jinwoong Lee and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i></p>
<p>TB5-F-5 17:30-17:45</p>	<p>Effects of High-Energy Electron Injection on MOSFET Reliability</p> <p>Daehwan Kim¹, Jae Hoon Park², Chang Kyun Kim², and Seongjae Cho¹ ¹<i>Department of Electronic Engineering, Gachon University,</i> ²<i>The Attached Institute of ETRI</i></p>
<p>TB5-F-6 17:45-18:00</p>	<p>Hot Carrier Injection Analysis of Tunnel Field Effect Transistors</p> <p>Jae Seung Woo, Jang Woo Lee, and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i></p>